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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Wendell P. Noble et al.

Title: ULTRA HIGH DENSITY FLASH MEMORY

Docket No.: 303.330US3
Filed: May 29, 2001
Examiner: Jack Chen

Serial No.: 09/866,938
Due Date: N/A
Group Art Unit: 2813

Commissioner for Patents
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

X A return postcard.
X A Supplemental Information Disclosure Statement (1 pg.), Form 1449 (6 pgs.), and copies of 120 cited references.
X A Communication Concerning Co-Pending Applications (3 pgs.).

Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938, Minneapolis, MN 55402 (612-373-6900)

By: _____
Atty: Raymond R. Berdie
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Filed:	May 29, 2001	Docket:	303.330US3
Title:	ULTRA HIGH DENSITY FLASH MEMORY		

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Supplemental Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Account No. 19-0743 in order to have this Supplemental Information Disclosure Statement considered.

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

WENDELL P. NOBLE ET AL.

By their Representatives,

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P.O. Box 2938
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Date 5-7-2002 By _____
Raymond R. Berdie
Reg. No. 50,769

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Name: Gina Johns

Signature: Gina Johns

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known	
Application Number	09/866938
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First Named Inventor	Noble Jr., Wendell
Group Art Unit	2813
Examiner Name	Chen, Jack

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Attorney Docket No: 00303.330US3

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Group Art Unit	2813
Examiner Name	Chen, Jack

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Examiner Initials*	Cite No [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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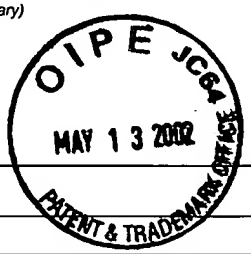

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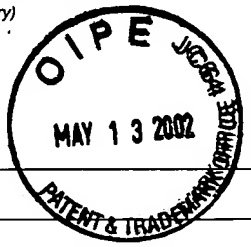

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